

Vishay Siliconix

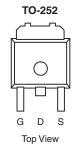
P-Channel 40-V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$r_{DS(on)}\left(\Omega\right)$	I _D (A)		
- 40	0.013 at $V_{GS} = -10 \text{ V}$	- 60 ^a		
	0.022 at V _{GS} = - 4.5 V	- 48		

FEATURES

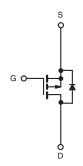
- TrenchFET® Power MOSFET
- 175 °C Junction Temperature





Drain Connected to Tab

Ordering Information: SUD50P04-13L-E3 (Lead (Pb)-free)



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 2$	5 °C, unless othe	rwise noted			
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	- 40	V	
Gate-Source Voltage		V _{GS}	± 20	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	
0 11 D 1 O 1h	T _C = 25 °C	_	- 60°		
Continuous Drain Current ^b	T _C = 100 °C	I _D	- 43		
Pulsed Drain Current		I _{DM}	- 100		
Continuous Source Current (Diode Conduction)		I _S	- 60°		
Avalanche Current	. 04	I _{AS}	- 40		
Avalanche Energy,	L = 0.1 mH	E _{AS}	80	mJ	
b. b b	T _C = 25 °C	В	93.7 ^b	10/	
Maximum Power Dissipation ^b	T _A = 25 °C	P _D	3 ^a	W	
Operating Junction and Storage Temperature Range	·	T _J , T _{stg}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^a	t ≤ 10 sec	- R _{thJA}	15	18	°C/W	
	Steady State		40	50		
Maximum Junction-to-Case (Drain)		R_{thJC}	1.3	1.8		

Notes:

- a. Surface Mounted on 1" x 1" FR4 board.
- b. See SOA curve for voltage derating.
- b. Calculated based on maximum allowed Junction Temperature. Package limitation current is 50 A.

SUD50P04-13L

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SPECIFICATIONS T _J = 25 °C, unless otherwise noted								
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit		
Static								
Drain-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 \text{ V, } I_D = -250 \mu\text{A}$	- 40			V		
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1.0		- 3.0] v		
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA		
Zero Gate Voltage Drain Current	lasa	$V_{DS} = -40 \text{ V}, V_{GS} = 0 \text{ V}$			- 1			
	I _{DSS}	$V_{DS} = -40 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 125 \text{ °C}$			- 50	μΑ		
On-State Drain Current ^a	I _{D(on)}	V _{DS} = - 5 V, V _{GS} = - 10 V	- 50			Α		
Drain-Source On-State Resistance ^a		V _{GS} = - 10 V, I _D = - 30 A		0.0105	0.013	Ω		
	r _{DS(on)}	V _{GS} = - 10 V, I _D = - 30 A, T _J = 125 °C			0.020			
		V _{GS} = - 4.5 V, I _D = - 20 A		0.017	0.022	1		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 30 A	15			S		
Dynamic ^b								
Input Capacitance	C _{iss}	V _{DS} = - 25 V, V _{GS} = 0 V, f = 1 MHz		3120		pF		
Output Capacitance	C _{oss}			440				
Reverse Transfer Capacitance	C _{rss}			320				
Gate Resistance	R_g	f = 1 MHz		4.3		Ω		
Total Gate Charge ^c	Qg			63	95			
Gate-Source Charge ^c	Q _{gs}	V _{DS} = - 20 V, V _{GS} = - 10 V, I _D = - 50 A		13		nC		
Gate-Drain Charge ^c	Q _{gd}			16				
Turn-On Delay Time ^c	t _{d(on)}			15	25			
Rise Time ^c	t _r	V_{DD} = - 20 V, R_L = 0.4 Ω $I_D \cong$ - 50 A, V_{GEN} = - 10 V, R_g = 2.5 Ω		18	30	ns		
Turn-Off Delay Time ^c	t _{d(off)}			60	90			
Fall Time ^c	t _f			47	70			
Drain-Source Body Diode Characteristic	s			•				
Pulse Current	I _{SM}				- 100			
Forward Voltage ^a	V _{SD}	I _F = - 50 A, V _{GS} = 0 V		- 1.0	- 1.5	V		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 50 A, di/dT = 100 A/μs		36	55	ns		

Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

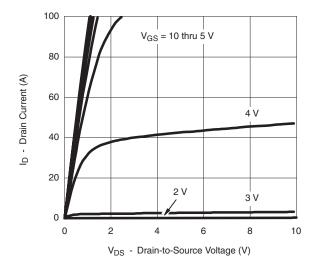
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



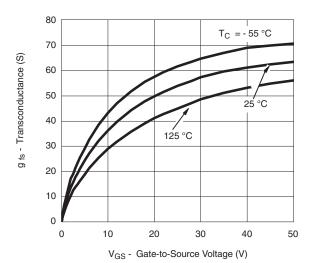


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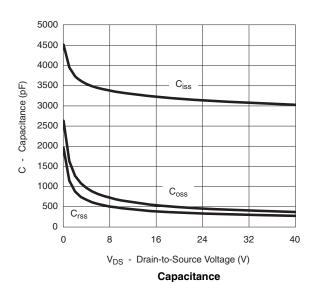
TYPICAL CHARACTERISTICS 25 °C unless noted

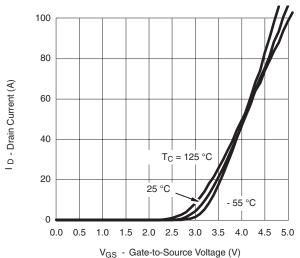


Output Characteristics

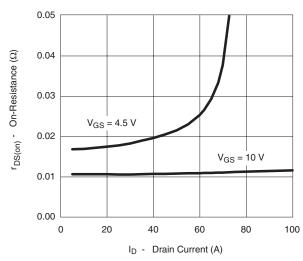


Transconductance

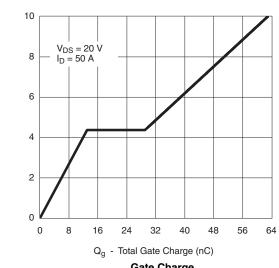




Transfer Characteristics



On-Resistance vs. Drain Current



Gate Charge

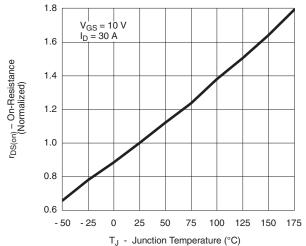
Document Number: 73009 S-71660-Rev. B, 06-Aug-07 V GS - Gate-to-Source Voltage (V)

SUD50P04-13L

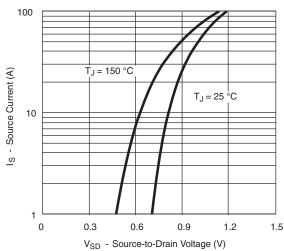
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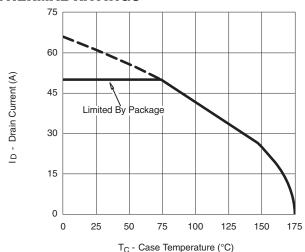


On-Resistance vs. Junction Temperature

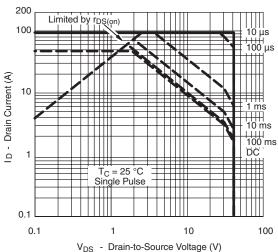


Source-Drain Diode Forward Voltage

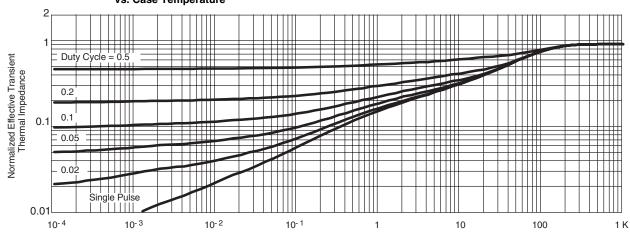
THERMAL RATINGS



Maximum Avalanche Drain Current vs. Case Temperature



Safe Operating Area

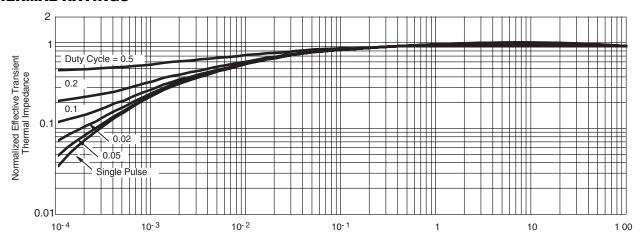


Square Wave Pulse Duration (sec)
Normalized Thermal Transient Impedance, Junction-to-Ambient



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THERMAL RATINGS



Square Wave Pulse Duration (sec)
Normalized Thermal Transient Impedance, Junction-to-Case

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